

L 44600-66

ACC NR: AP6030959

and a gain relatively lower than that of GaAs, expressed in a linear approximation as
 $k = 3.4 \times 10^{-3} j \text{ cm}^{-1}$, where j (amp/cm⁻²) is the current density. The latter can be
due to a lower (than GaAs) quantum yield and to a thick active layer (8-10 μ).
The differential efficiencies of the InP laser made it possible to deliver pulsed
power of 7 watts at 75 amp at the liquid N temperature. Orig. art. has: 2 tables,
2 figures, and 3 formulas. [YK]

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Card 3/3 LJM

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CIA-RDP86-00513R001961830011-1

End reel

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672

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